# **High-Power Industrial Transistors**

NPN silicon power transistor designed for applications in industrial and commercial equipment including high fidelity audio amplifiers, series and shunt regulators and power switches.

- Collector –Emitter Sustaining Voltage VCEO(sus) = 140 Vdc (Min)
- Excellent Second Breakdown Capability

2N3442

10 AMPERE
POWER TRANSISTOR
NPN SILICON
140 VOLTS
117 WATTS



CASE 1-07 TO-204AA (TO-3)

### \*MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	140	Vdc
Collector–Base Voltage	V <sub>CB</sub>	160	Vdc
Emitter–Base Voltage	V <sub>EB</sub>	7.0	Vdc
Collector Current — Continuous Peak	lC	10 15**	Adc
Base Current — Continuous Peak	lВ	7.0 —	Adc
Total Power Dissipation @ T <sub>C</sub> = 25°C Derate above 25°C	PD	117 0.67	Watts W/°C
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>Stg</sub>	-65 to +200	°C

### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{ heta JC}$	1.5	°C/W

<sup>\*</sup> Indicates JEDEC Registered Data.

<sup>\*\*</sup> This data guaranteed in addition to JEDEC registered data.

## **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage (I <sub>C</sub> = 200 mAdc, I <sub>B</sub> = 0)	VCEO(sus)	140	_	Vdc
Collector Cutoff Current (V <sub>CE</sub> = 140 Vdc, I <sub>B</sub> = 0)	ICEO	_	200	mAdc
Collector Cutoff Current (V <sub>CE</sub> = 140 Vdc, V <sub>BE</sub> (off) = 1.5 Vdc) (V <sub>CE</sub> = 140 Vdc, V <sub>BE</sub> (off) = 1.5 Vdc, T <sub>C</sub> = 150°C)	ICEX	_ _	5.0 30	mAdc
Emitter Cutoff Current (VBE = 7.0 Vdc, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	5.0	mAdc
ON CHARACTERISTICS (1)				
DC Current Gain (I <sub>C</sub> = $3.0$ Adc, V <sub>CE</sub> = $4.0$ Vdc) (I <sub>C</sub> = $10$ Adc, V <sub>CE</sub> = $4.0$ Vdc)	hFE	20 7.5	70 —	_
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 10 Adc, I <sub>B</sub> = 2.0 Adc)	VCE(sat)	_	5.0	Vdc
Base–Emitter On Voltage (I <sub>C</sub> = 10 Adc, V <sub>CE</sub> = 4.0 Vdc)	VBE(on)	_	5.7	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain — Bandwidth Product (2) (I <sub>C</sub> = 2.0 Adc, V <sub>CE</sub> = 4.0 Vdc, f <sub>test</sub> = 40 kHz)	fτ	80	_	kHz
Small–Signal Current Gain (I <sub>C</sub> = 2.0 Adc, V <sub>CE</sub> = 4.0 Vdc, f = 1.0 kHz)	h <sub>fe</sub>	12	72	_

<sup>\*</sup> Indicates JEDEC Registered Data.

#### NOTES

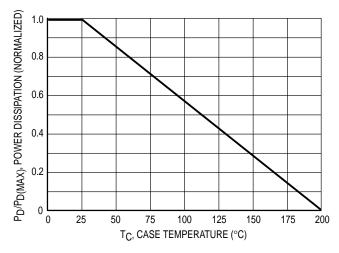


Figure 1. Power Derating

<sup>1.</sup> Pulse Test: Pulse Width = 300  $\mu$ s, Duty Cycle  $\leq$  2.0%.

<sup>2.</sup>  $f_T = |h_{fe}| \bullet f_{test}$ 

### **ACTIVE REGION SAFE OPERATING AREA INFORMATION**

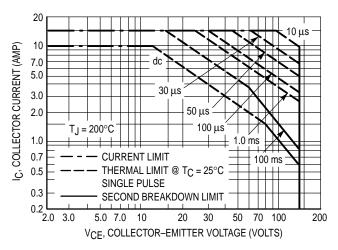


Figure 2. 2N3442

There are two limitations on the power–handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate IC – VCE limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 2 is based on  $T_{J(pk)} = 200^{\circ}C$ ;  $T_{C}$  is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown.

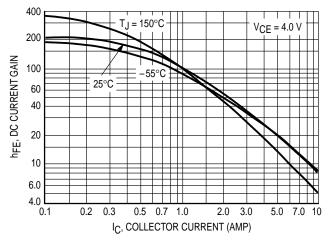


Figure 3. DC Current Gain

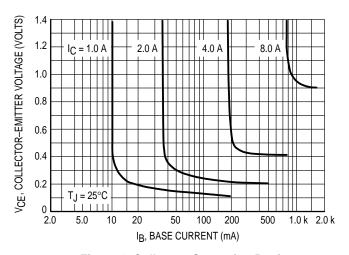
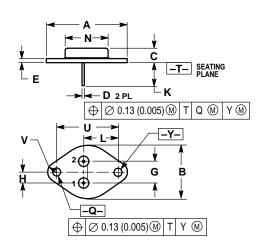


Figure 4. Collector-Saturation Region

#### PACKAGE DIMENSIONS



- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
- ALL RULES AND NOTES ASSOCIATED WITH
   REFERENCED TO-204AA OUTLINE SHALL APPLY.

	INC	INCHES MILLIMETERS		
DIM	MIN	MAX	MIN	MAX
Α	1.550 REF		39.37 REF	
В	-	1.050		26.67
C	0.250	0.335	6.35	8.51
D	0.038	0.043	0.97	1.09
Е	0.055	0.070	1.40	1.77
G	0.430 BSC		10.92 BSC	
Н	0.215 BSC		5.46 BSC	
K	0.440	0.480	11.18	12.19
L	0.665 BSC		16.89 BSC	
N		0.830		21.08
ø	0.151	0.165	3.84	4.19
U	1.187 BSC		30.15 BSC	
V	0.131	0.188	3.33	4 77

STYLE 1: PIN 1. BASE 2. EMITTER CASE: COLLECTOR

**CASE 1-07** TO-204AA (TO-3) **ISSUE Z** 

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